L Number	Hits	Search Text	DB	Time stamp
–	513	@ad<=20021030 and (257/239).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:01
–	694	@ad<=20021030 and (257/314).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 12:44
–	1615	@ad<=20021030 and (257/316).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 12:45
–	225	@ad<=20021030 and (257/318).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 12:45
–	255	@ad<=20021030 and (257/319).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 12:46
–	1419	@ad<=20021030 and (257/315).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 14:10
–	267	@ad<=20021030 and (438/201).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 12:47
–	157	@ad<=20021030 and (438/211).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 12:48
–	151	@ad<=20021030 and (438/212).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 12:48
–	1389	@ad<=20021030 and (438/257).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 12:49
–	335	@ad<=20021030 and (438/593).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:35
–	2	("6214668").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 12:52
–	1	"5050125".PN.	USPAT	2003/10/20 12:53
–	1	"5268318".PN.	USPAT	2003/10/20 12:54
–	1	"6064099".PN.	USPAT	2003/10/20 12:54
–	1	"5747849".PN.	USPAT	2003/10/20 12:55

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–	124	@ad<=20021030 and 'flash memory' same 'doped' same 'trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:01
–	0	@ad<=20021030 and 'flash memory' same 'doped trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:04
–	98	@ad<=20021030 and 'doped trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 14:21
–	4	@ad<=20021030 and 'doped trench' and 'floating gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:36
–	1	@ad<=20021030 and 'doped trench' and 'EEPROM'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:08
–	3	@ad<=20021030 and 'floating gate' same 'trench' near2 'dope'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:11
–	1	@ad<=20021030 and 'floating gate' same 'trench' near 'dope'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:40
–	18	@ad<=20021030 and 'floating gate' same 'trench' same 'dope'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:22
–	3	@ad<=20021030 and 'EEPROM' same 'trench' same 'dope'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:22
–	1	@ad<=20021030 and 'doped trench' and 'non-volatile'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:37
–	590	@ad<=20021030 and 'flash memory'and 'channel hot electron injection'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:42
–	156	@ad<=20021030 and 'flash memory'and 'channel hot electron injection' and 'trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:50
–	0	@ad<=20021030 and 'flash memory'and 'channel hot electron injection' and 'doping trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:50
–	0	@ad<=20021030 and 'flash memory'and 'channel hot electron injection' and 'dope trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 13:50

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-	397	@ad<=20021030 and (257/315).ccls. and 'trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 14:10
-	3	@ad<=20021030 and 'doped trench' and 'control gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 14:21
-	9	@ad<=20021030 and hung-chih-wei.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 14:51
-	141	@ad<=20021030 and Powerchip-semiconductor-corp.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/20 14:51
-	1	"5587332".PN.	USPAT	2003/10/20 14:53
-	1	"5717636".PN.	USPAT	2003/10/20 14:53
-	1329	@ad<=20021030 and 'flash memory' same 'contact'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:11
-	568	@ad<=20021030 and 'flash memory' and 'contact' and 'well' same 'junction'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:12
-	15	@ad<=20021030 and 'flash memory' same 'contact' same 'well' same 'junction'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:23
-	29	@ad<=20021030 and 'flash memory' and 'Fowler-Norheim'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:30
-	39	@ad<=20021030 and 'EEPROM' and 'Fowler-Norheim'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:31
-	10	@ad<=20021030 and 'Fowler-Norheim' and 'trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:31
-	59	@ad<=20021030 and (257/550).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:36
-	101	@ad<=20021030 and (257/549).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:36
-	40	@ad<=20021030 and (257/548).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 10:27

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-	237	@ad<=20021030 and 'non-volatile memory' same 'trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:41
-	152	@ad<=20021030 and 'non-volatile memory' and 'trench' with 'doped'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 11:27
-	3	@ad<=20021030 and 'non-volatile memory' same 'source line contact'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 09:56
-	225	@ad<=20021030 and (257/296).ccls. and 'non-volatile'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 10:28
-	161	@ad<=20021030 and (257/296).ccls. and 'non-volatile memory'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 10:28
-	42	@ad<=20021030 and 'source' with 'connect' with 'trench' with 'doped'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/21 11:28

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